

adding said impurity element to said semiconductor layer through said first conductive layer using said second conductive layer with said fourth width as a mask to form a low concentration impurity region; and

etching said first conductive layer to form a third electrode comprising a laminate structure of said first conductive layer with a fifth width and said second conductive layer with said fourth width.

33. (Amended) A method of manufacturing a semiconductor device comprising steps of:

forming a semiconductor layer on an insulating surface;

forming an insulating film on said semiconductor layer;

laminating a first conductive film and a second conductive film on said insulating film;

forming a second conductive layer with a first width;

adding an impurity element to said semiconductor layer using said second conductive layer with said first width as a mask to form a high concentration impurity region;

etching said second conductive layer to form said second conductive layer with a second width;

adding an impurity element to said semiconductor layer through said first conductive film using said second conductive layer with said second width as a mask to form a low concentration impurity region; and

etching said first conductive film to form an electrode comprising a laminate structure of a conductive layer with a third width and said second conductive layer with said second width. --